

# NMLU1210

## Full Bridge Rectifier

Dual 20 V N-Channel with dual 3.2 A Schottky Barrier Diode, 4.0 x 4.0 x 0.5 mm  $\mu$ Cool™ Package

### Features

- Full-Bridge Rectifier Block
- Up to 3.2 A operation
- Low  $R_{DS(on)}$  MOSFET to minimize conduction loss
- Low gate charge MOSFET
- Low  $V_F$  Schottky diode
- Ultra Low Inductance Package
- This Device uses Halogen-Free Molding Compound
- These are Pb-Free Devices

### Applications

- Wireless Charging
- AC-DC Rectification
- Optimized for Power Management Applications for Portable Products, such as Cell Phones, PMP, DSC, GPS, and others

### RECTIFIER MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Value	Unit	
Input voltage between two MOSFET drain	$V_{LL}$	20	V	
Bridge Operating Junction and Storage Temperature	$T_J, T_{STG}$	-55 to 125	$^\circ\text{C}$	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	$T_L$	260	$^\circ\text{C}$	
Continuous Drain Current $R_{JA}$ (Note 1)	$I_O$	$T_A = 25^\circ\text{C}$	2.2	A
		$T_A = 85^\circ\text{C}$	1.16	
Power Dissipation $R_{JA}$ (Note 1)	$P_D$	$T_A = 25^\circ\text{C}$	1.2	W
		$T_A = 85^\circ\text{C}$	0.47	
Continuous Drain Current $R_{JA} t < 5$ s (Note 1)	$I_O$	$T_A = 25^\circ\text{C}$	3.2	A
		$T_A = 85^\circ\text{C}$	1.88	
Power Dissipation $R_{JA} t < 5$ s (Note 1)	$P_D$	$T_A = 25^\circ\text{C}$	2.34	W
		$T_A = 85^\circ\text{C}$	0.94	
Continuous Drain Current $R_{JA}$ (Note 2)	$I_O$	$T_A = 25^\circ\text{C}$	1.16	A
		$T_A = 85^\circ\text{C}$	0.6	
Power Dissipation $R_{JA}$ (Note 2)	$P_D$	$T_A = 25^\circ\text{C}$	0.47	W
		$T_A = 85^\circ\text{C}$	0.185	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
2. Surface-mounted on FR4 board using the minimum recommended pad size of 30 mm<sup>2</sup>, 2 oz. Cu.



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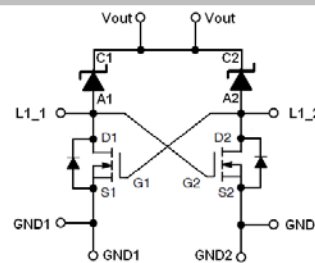
<http://onsemi.com>

### MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	$I_D$ MAX
20 V	23 m $\Omega$ @ 4.5 V	3.2 A
	17 m $\Omega$ @ 10 V	

### SCHOTTKY DIODE

$V_R$ MAX	$V_F$ TYP	$I_F$ MAX
20 V	0.45 V	3.2 A



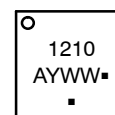
### RECTIFIER

4.0 4.0 mm  $\mu$ Cool Pin Connections (Top View)

### MARKING DIAGRAM



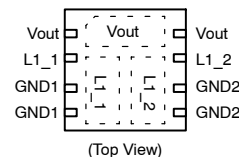
UDFN  
CASE 517BS



1210 = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
▪ = Pb-Free Package

(\*Note: Microdot may be in either location)

### PIN CONNECTIONS



### ORDERING INFORMATION

Device	Package	Shipping†
NMLU1210TWG	UDFN (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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## THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	82.5	°C/W
Junction-to-Ambient – $t \leq 5$ s (Note 3)	$R_{\theta JA}$	42.5	
Junction-to-Ambient – Steady State min Pad (Note 4)	$R_{\theta JA}$	209	

3. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).  
 4. Surface-mounted on FR4 board using the minimum recommended pad size of 30 mm<sup>2</sup>, 2 oz. Cu.

## BRIDGE ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>ON CHARACTERISTICS</b>						
Rectifying Forward Voltage (Note 5)	$V_{fd2}$	Input voltage $V_{LL} = \pm 5$ V; The output current of Rectifier $I_{out} = 2$ A		0.45	.56	V
Rectifier leakage current	$I_{leak}$	Input voltage $V_{LL} = 16$ V; No Load on the Rectifier output		31	1000	uA
Rectifier Reverse leakage current	$I_{rleak}$	Input voltage $V_{LL} = 0$ V; The output voltage of the Rectifier $V_{out} = 5$ V		21	1000	uA

5. Pulse Test: pulse width  $\leq 300$   $\mu\text{s}$ , duty cycle  $\leq 2\%$

## MOSFET ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$ , $I_D = 250$ $\mu\text{A}$	1.2		2.2	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)} / T_J$			4		mV/°C
Drain-to-Source On Resistance (Note 6)	$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 3.2$ A		17	26	m $\Omega$
		$V_{GS} = 4.5$ V, $I_D = 3.2$ A		23	32	
Forward Transconductance	$g_{FS}$	$V_{DS} = 10$ V, $I_D = 2.0$ A		3.5		S

## DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage (Note 6)	$V_{SD}$	$V_{GS} = 0$ V, $I_S = 2.0$ A	$T_J = 25^\circ\text{C}$		0.79	V
			$T_J = 125^\circ\text{C}$		0.65	

6. Pulse Test: pulse width  $\leq 300$   $\mu\text{s}$ , duty cycle  $\leq 2\%$

## SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Maximum Instantaneous Forward Voltage (Note 7)	$V_F$	$I_F = 1.0$ A		0.36		V
		$I_F = 2.0$ A		0.41		
Maximum Instantaneous Reverse Current	$I_R$	$V_R = 20$ V		0.04		mA

7. Pulse Test: pulse width  $\leq 300$   $\mu\text{s}$ , duty cycle  $\leq 2\%$

## SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS ( $T_J = 100^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Maximum Instantaneous Forward Voltage (Note 8)	$V_F$	$I_F = 1.0$ A		0.29		V
		$I_F = 2.0$ A		0.36		
Maximum Instantaneous Reverse Current	$I_R$	$V_R = 20$ V		4		mA

8. Pulse Test: pulse width  $\leq 300$   $\mu\text{s}$ , duty cycle  $\leq 2\%$   
 9. For detailed MOSFET and Diode parameters, please refer to the ON Semiconductor datasheets of NTTFS4930N and MBR230LSFT1G. The test on each individual die is limited to the system package.

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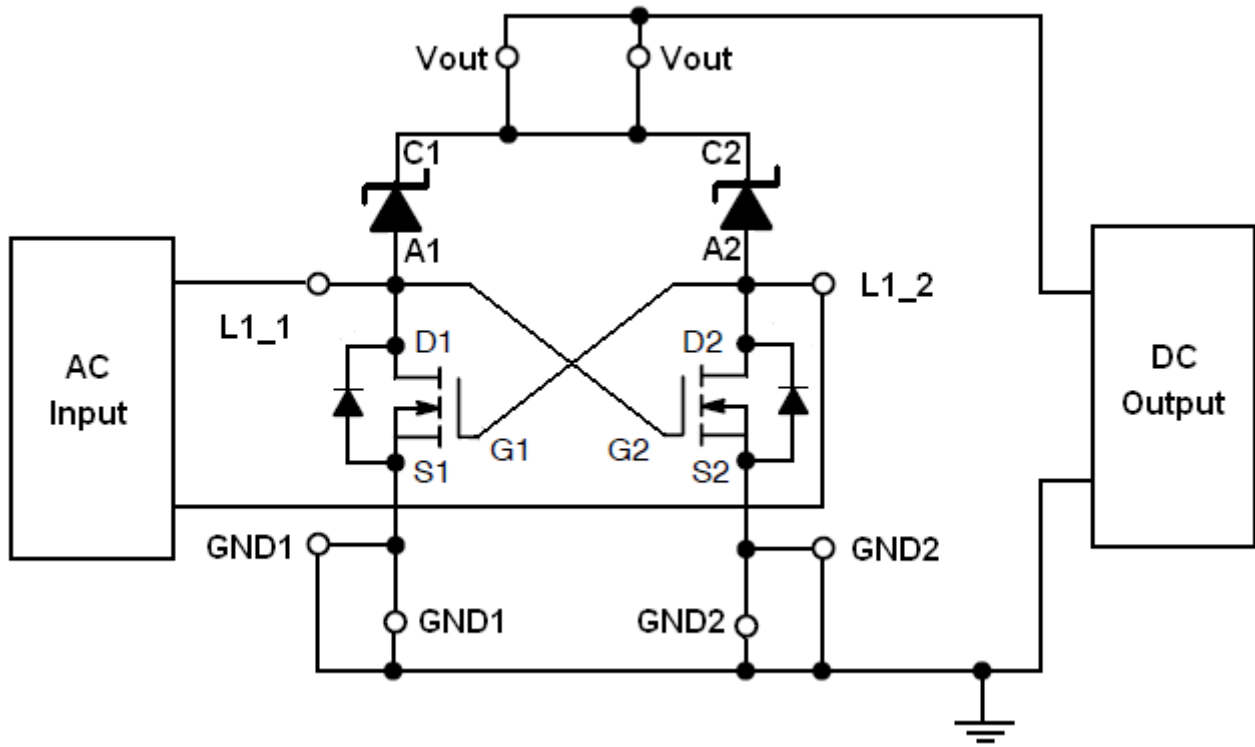


Figure 1. Typical Application Circuit

GND1 and GND2 are not internally connected. The user should make the connection in the PCB design.

TYPICAL PERFORMANCE CURVES

( $T_J = 25^\circ\text{C}$  unless otherwise specified)

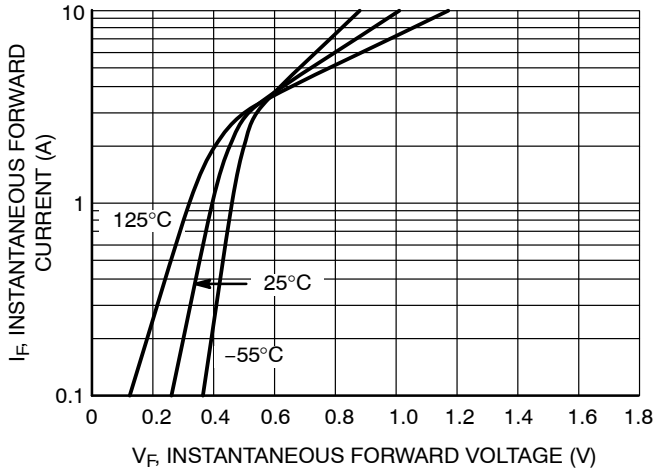


Figure 2. Bridge Typical Forward Voltage Drop at  $V_{in} \geq 5\text{ V}$

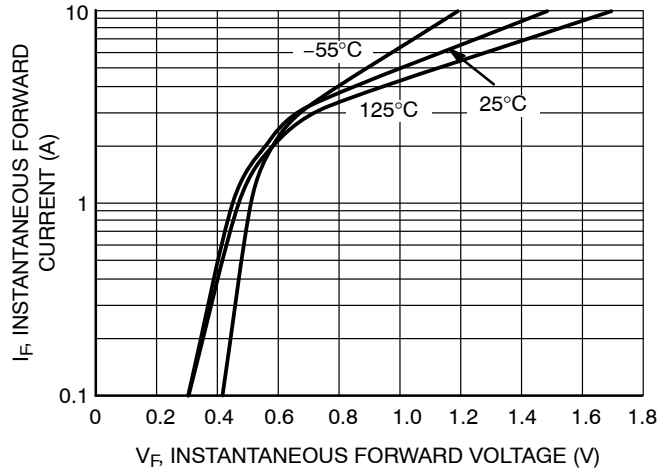


Figure 3. Bridge Maximum Forward Voltage Drop at  $V_{in} \geq 5\text{ V}$

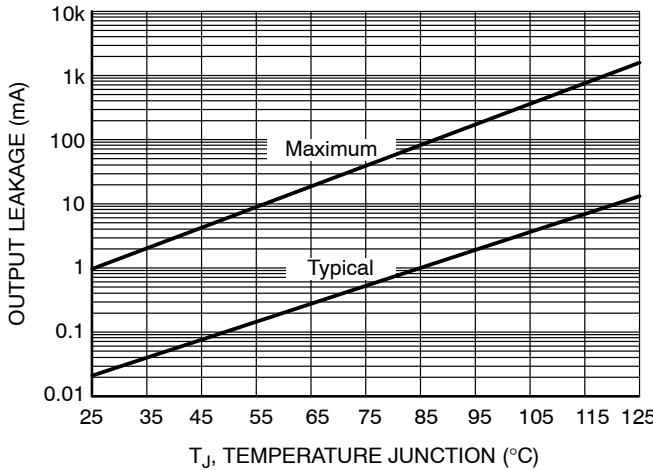


Figure 4. Output Leakage at 5 V Bias vs. Junction Temperature

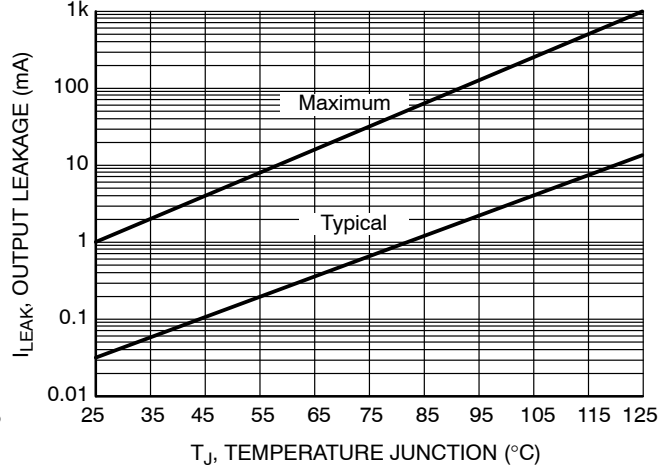


Figure 5. Input Leakage at 16 V vs. Junction Temperature

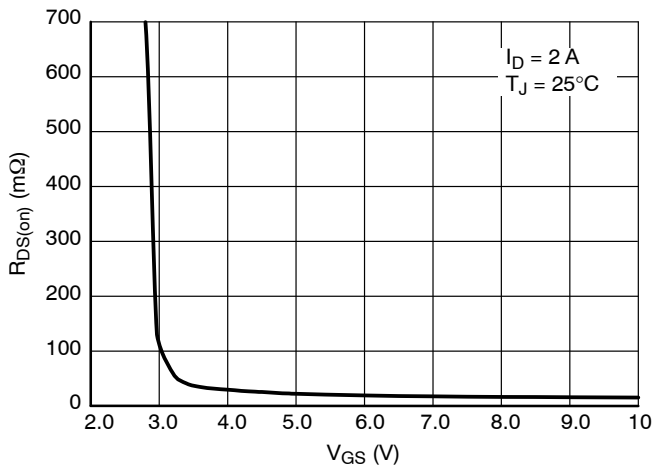


Figure 6. FET Typical On-Resistance vs. Gate-to-Source Voltage ( from 3 V to 10 V)

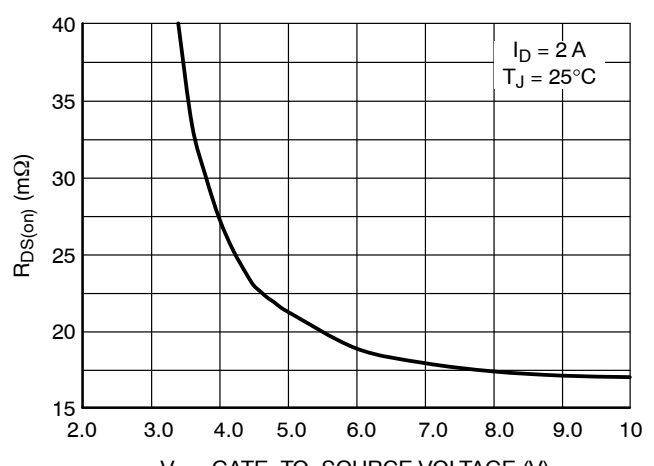
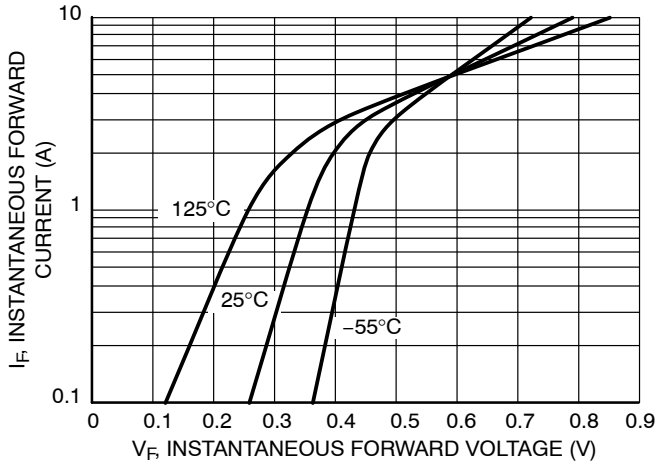


Figure 7. FET Typical On-Resistance vs. Gate-to-Source Voltage

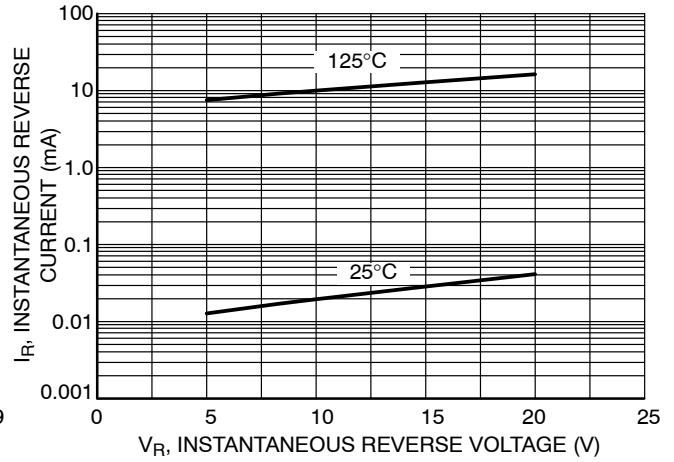
# NMLU1210

## TYPICAL PERFORMANCE CURVES

( $T_J = 25^\circ\text{C}$  unless otherwise specified)



**Figure 8. Schottky Typical Forward Current vs. Forward Voltage**



**Figure 9. Schottky Typical Reverse Current vs. Reverse Voltage**

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

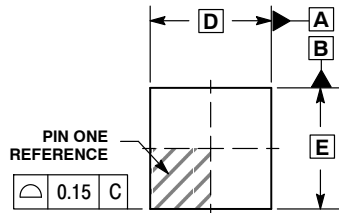
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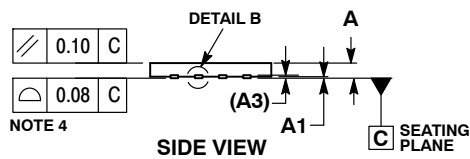
### UDFN8 4x4, 0.8P CASE 517BS ISSUE A

DATE 06 SEP 2011

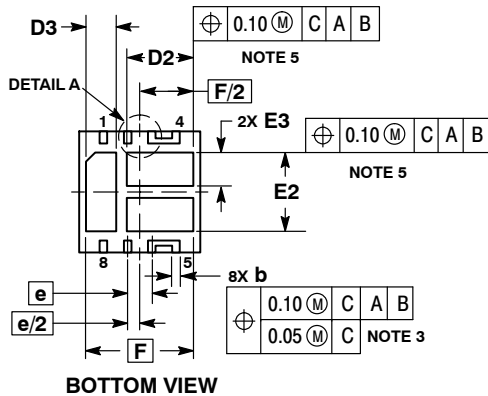
SCALE 2:1



TOP VIEW

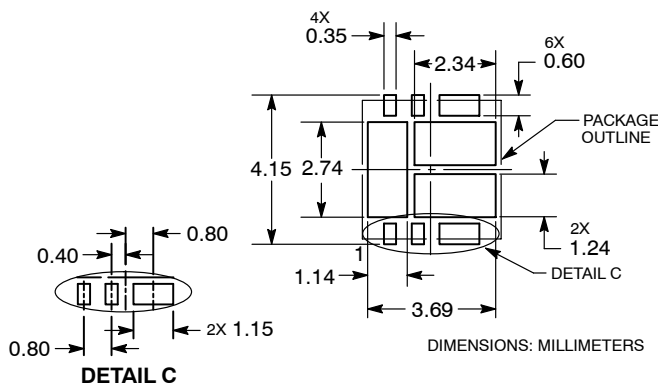


SIDE VIEW



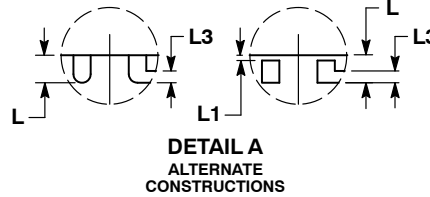
BOTTOM VIEW

### RECOMMENDED SOLDERING FOOTPRINT\*

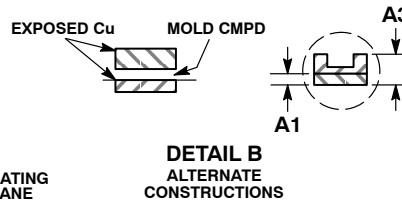


DETAIL C

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



DETAIL A  
ALTERNATE  
CONSTRUCTIONS



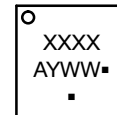
DETAIL B  
ALTERNATE  
CONSTRUCTIONS

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.25MM FROM TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
5. POSITIONAL TOLERANCE APPLIES TO ALL OF THE EXPOSED PADS.

MILLIMETERS		
DIM	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A3	0.13	REF
b	0.20	0.30
D	4.00	BSC
D2	2.10	2.30
D3	0.90	1.10
E	4.00	BSC
E2	2.50	2.70
E3	1.00	1.20
e	0.80	BSC
F	3.55	BSC
L	0.30	0.50
L1	0.00	0.15
L3	0.13	0.23

### GENERIC MARKING DIAGRAM\*



- XXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

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